INTEGRATED CIRCUITS



Product specification

2003 Sep 09



GreenChip[™]II SMPS control IC

FEATURES

Distinctive features

- Universal mains supply operation (70 to 276 V AC)
- High level of integration; giving a low external component count.

Green features

- Valley or zero voltage switching for minimum switching losses
- Efficient quasi-resonant operation at high power levels
- Frequency reduction at low power standby for improved system efficiency (≤3 W)
- Cycle skipping mode at very low loads.

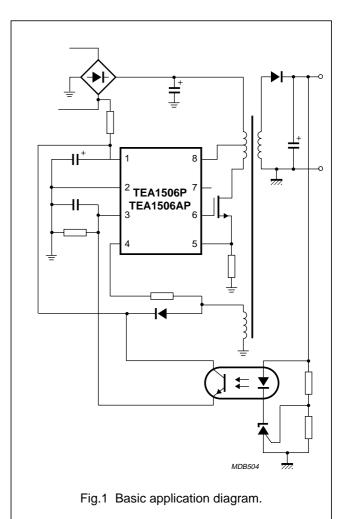
Protection features

- Safe restart mode for system fault conditions
- Continuous mode protection by means of demagnetization detection (zero switch-on current)
- Accurate and adjustable overvoltage protection (latched in TEA1506; safe restart in TEA1506A)
- Short winding protection
- Undervoltage protection (foldback during overload)
- Overtemperature protection
- Low and adjustable overcurrent protection trip level
- Soft (re)start.

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT

APPLICATIONS

Besides typical application areas, i.e. TV and monitor supplies, the device can be used in adapters and chargers and all applications that demand an efficient and cost-effective solution up to 150 W. Unlike the other GreenChip[™]II control ICs, the TEA1506 has no internal high voltage start-up source and needs to be started by means of an external bleeder resistor.



GENERAL DESCRIPTION

The GreenChip^{TM(1)}II is the second generation of green Switched Mode Power Supply (SMPS) control ICs. A high level of integration leads to a cost effective power supply with a low number of external components.

(1) GreenChip is a trademark of Koninklijke Philips Electronics N.V.

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT

The special built-in green functions allow the efficiency to be optimum at all power levels. This holds for quasi-resonant operation at high power levels, as well as fixed frequency operation with valley switching at medium power levels. At low power (standby) levels, the system operates at a reduced frequency and with valley detection.

Highly efficient and reliable supplies can easily be designed using the GreenChip™II control IC.

TYPE NUMBER		PACKAGE	
I TPE NUMBER	NAME	DESCRIPTION	VERSION
TEA1506P	DIP8	plastic dual in-line package; 8 leads (300 mil)	SOT97-1
TEA1506AP			
TEA1506T	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
TEA1506AT			

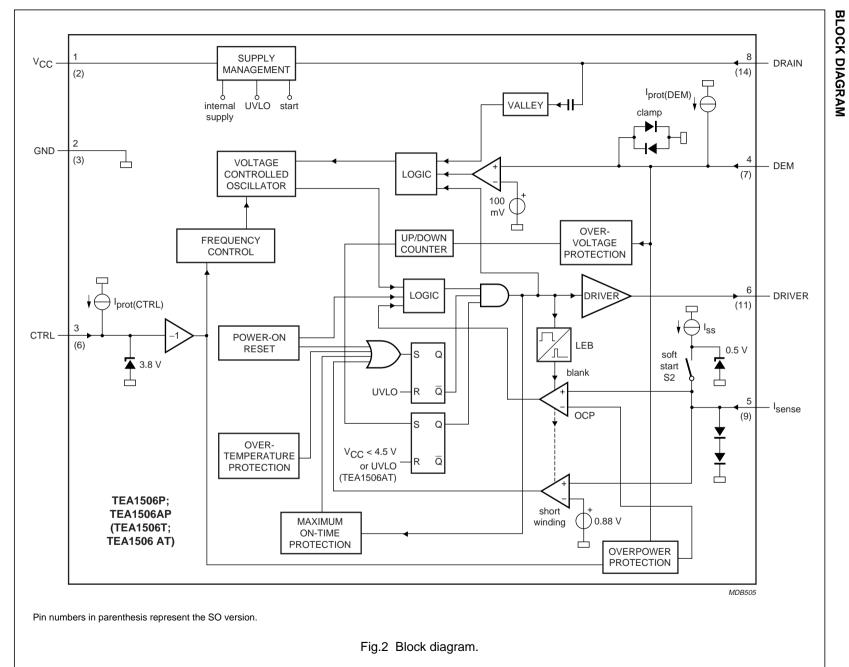
ORDERING INFORMATION

Philips Semiconductors

Product specification

GreenChip™II SMPS control IC

TEA1506P; TEA1506T; TEA1506AP; TEA1506AT



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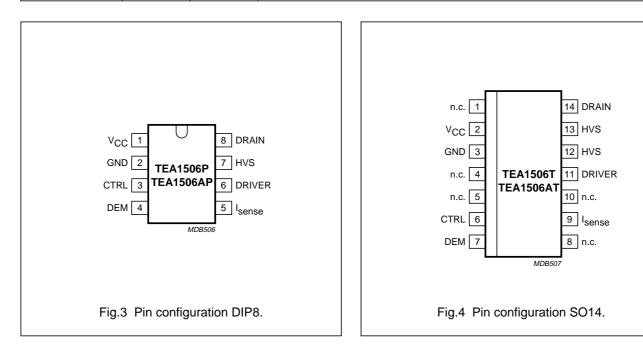
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TEA1506P; TEA1506AP; TEA1506T; TEA1506AT

PINNING

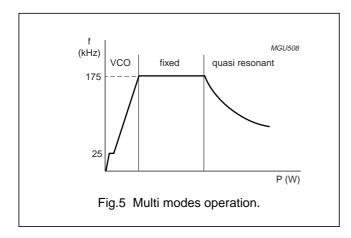
SYMBOL	PIN		DESCRIPTION				
STWBOL	DIP8	SO14	DESCRIPTION				
V _{CC}	1	2	supply voltage				
GND	2	3	ground				
CTRL	3	6	control input				
DEM	4	7	input from auxiliary winding for demagnetization timing; overvoltage and overpower protection				
I _{sense}	5	9	programmable current sense input				
DRIVER	6	11	gate driver output				
HVS	7	12, 13	high voltage safety spacer; not connected				
DRAIN	8	14	drain of external MOS switch; input for valley sensing and initial internal supply				
n.c.	-	1, 4, 5, 8, 10	not connected				



FUNCTIONAL DESCRIPTION

The TEA1506 is the controller of a compact flyback converter, and is situated at the primary side. An auxiliary winding of the transformer provides demagnetization detection and powers the IC after start-up.

The TEA1506 can operate in multi modes (see Fig.5).



The next converter stroke is started only after demagnetization of the transformer current (zero current switching), while the drain voltage has reached the lowest voltage to prevent switching losses (green function). The primary resonant circuit of the primary inductance and drain capacitor ensures this quasi-resonant operation. The design can be optimized in such a way that zero voltage switching can be reached over almost the universal mains range.

To prevent very high frequency operation at lower loads, the quasi-resonant operation changes smoothly in fixed frequency PWM control.

At very low power (standby) levels, the frequency is controlled down, via the VCO, to a minimum frequency of approximately 25 kHz.

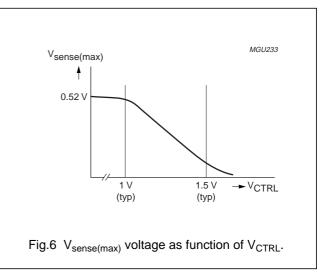
Start-up and undervoltage lock-out

Initially the IC is in the save restart mode. As long as V_{CC} is below the $V_{CC(\text{start})}$ level, the supply current is nearly zero.

The IC will activate the converter as soon as the voltage on pin V_{CC} passes the $V_{CC(start)}$ level.

The IC supply is taken over by the auxiliary winding as soon as the output voltage reaches its intended level.

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT



The moment the voltage on pin V_{CC} drops below the undervoltage lock-out level, the IC stops switching and re-enters the safe restart mode.

Supply management

All (internal) reference voltages are derived from a temperature compensated, on-chip band gap circuit.

Current mode control

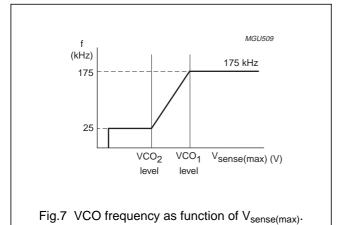
Current mode control is used for its good line regulation behaviour.

The 'on-time' is controlled by the internally inverted control voltage, which is compared with the primary current information. The primary current is sensed across an external resistor. The driver output is latched in the logic, preventing multiple switch-on.

The internal control voltage is inversely proportional to the external control pin voltage, with an offset of 1.5 V. This means that a voltage range from 1 to 1.5 V on pin CTRL will result in an internal control voltage range from 0.5 to 0 V (a high external control voltage results in a low duty cycle).

Oscillator

The maximum fixed frequency of the oscillator is set by an internal current source and capacitor. The maximum frequency is reduced once the control voltage enters the VCO control window. Then, the maximum frequency changes linearly with the control voltage until the minimum frequency is reached (see Figs 6 and 7).



Cycle skipping

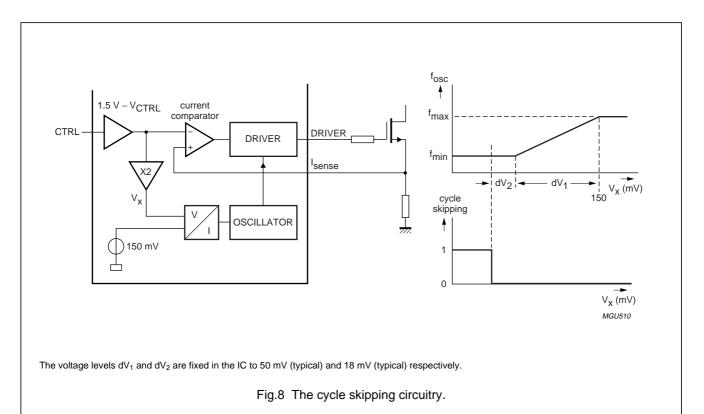
At very low power levels, a cycle skipping mode will be activated. A high control voltage will reduce the switching frequency to a minimum of 25 kHz. If the voltage on the control pin is raised even more, switch-on of the external power MOSFET will be inhibited until the voltage on the control pin has dropped to a lower value again (see Fig.8).

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TEA1506T; TEA1506AT

For system accuracy, it is not the absolute voltage on the control pin that will trigger the cycle skipping mode, but a signal derived from the internal VCO will be used.

Remark: If the no-load requirement of the system is such that the output voltage can be regulated to its intended level at a switching frequency of 25 kHz or above, the cycle skipping mode will not be activated.



Demagnetization

The system will be in discontinuous conduction mode all the time. The oscillator will not start a new primary stroke until the secondary stroke has ended.

Demagnetization features a cycle-by-cycle output short-circuit protection by immediately lowering the frequency (longer off-time), thereby reducing the power level.

Demagnetization recognition is suppressed during the first t_{suppr} time. This suppression may be necessary in applications where the transformer has a large leakage inductance, at low output voltages and at start-up.

If pin DEM is open-circuit or not connected, a fault condition is assumed and the converter will stop operating immediately. Operation will recommence as soon as the fault condition is removed.

Minimum and maximum 'on-time'

The minimum 'on-time' of the SMPS is determined by the Leading Edge Blanking (LEB) time. The IC limits the 'on-time' to 50 μ s. When the system desires an 'on-time' longer than 50 μ s, a fault condition is assumed (e.g. removed C_i in Fig.12), the IC will stop switching and enter the safe restart mode.

OverVoltage Protection (OVP)

An OVP mode is implemented in the GreenChip series. This works for the TEA1506 by sensing the auxiliary voltage via the current flowing into pin DEM during the secondary stroke. The auxiliary winding voltage is a well-defined replica of the output voltage. Any voltage spikes are averaged by an internal filter.

If the output voltage exceeds the OVP trip level, an internal counter starts counting subsequent OVP events. The counter has been added to prevent incorrect OVP detections which might occur during ESD or lightning events. If the output voltage exceeds the OVP trip level a few times and not again in a subsequent cycle, the internal counter will count down with twice the speed compared with counting-up. However, when typical 10 cycles of subsequent OVP events are detected, the IC assumes a true OVP and the OVP circuit switches the power MOSFET off. Next, the controller waits until the UVLO level is reached on pin V_{CC} . When V_{CC} drops to UVLO, capacitor C_{VCC} will be recharged to the V_{start} level.

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT

Regarding the TEA1506, the IC will not start switching again. Subsequently, $V_{\rm CC}$ will drop again to the UVLO level, etc.

Operation only recommences when the V_{CC} voltage drops below a level of about 4.5 V.

Regarding the TEA1506A, when the V_{start} level is reached, switching starts again (safe restart mode) when the V_{start} level is reached. This process is repeated as long as the OVP condition exists.

The output voltage $V_{o(OVP)}$ at which the OVP function trips, can be set by the demagnetization resistor, $R_{DEM}\!\!:$

$$\begin{split} &V_{o(OVP)} \ = \\ &\frac{N_s}{N_{aux}}\{I_{(OVP)(DEM)} \times R_{DEM} + V_{clamp(DEM)(pos)}\} \end{split}$$

where N_{s} is the number of secondary turns and N_{aux} is the number of auxiliary turns of the transformer.

Current I_{(OVP)(DEM)} is internally trimmed.

The value of R_{DEM} can be adjusted to the turns ratio of the transformer, thus making an accurate OVP possible.

Valley switching

A new cycle starts when the power MOSFET is switched on (see Fig.9). After the 'on-time' (which is determined by the 'sense' voltage and the internal control voltage), the switch is opened and the secondary stroke starts. After the secondary stroke, the drain voltage shows an oscillation

with a frequency of approximately $\frac{1}{2\times\pi\times\sqrt{(L_p\times C_d)}}$

where L_p is the primary self inductance of the transformer and C_d is the capacitance on the drain node.

As soon as the oscillator voltage is high again and the secondary stroke has ended, the circuit waits for the

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT

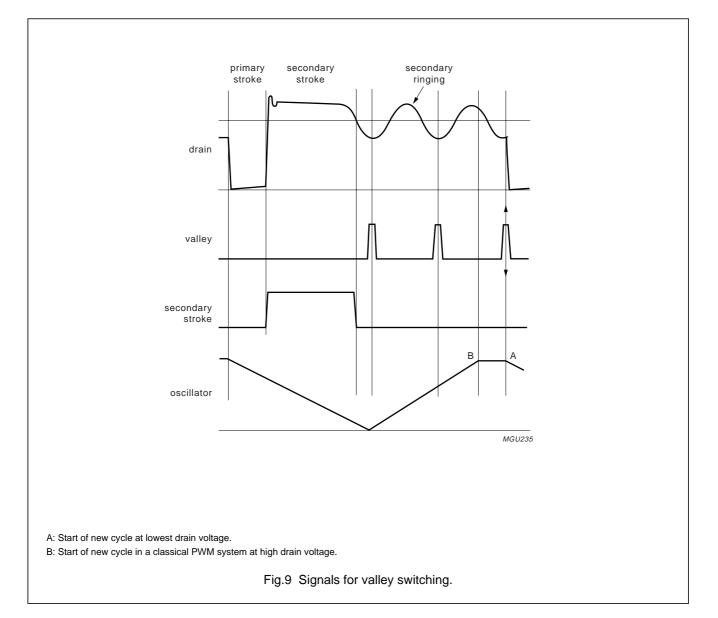
lowest drain voltage before starting a new primary stroke. This method is called valley detection.

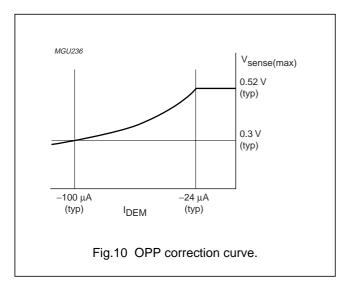
Figure 9 shows the drain voltage together with the valley signal, the signal indicating the secondary stroke and the oscillator signal.

In an optimum design, the reflected secondary voltage on the primary side will force the drain voltage to zero. Thus, zero voltage switching is very possible, preventing large

capacitive switching losses
$$\left(P = \frac{1}{2} \times C \times V^2 \times f\right)$$

and allowing high frequency operation, which results in small and cost effective inductors.





OverCurrent Protection (OCP)

The cycle-by-cycle peak drain current limit circuit uses the external source resistor to measure the current accurately. This allows optimum size determination of the transformer core (cost issue). The circuit is activated after the leading edge blanking time, t_{leb} . The OCP circuit limits the 'sense' voltage to an internal level.

OverPower Protection (OPP)

During the primary stroke, the rectified mains input voltage is measured by sensing the current drawn from pin DEM. This current is dependent on the mains voltage, according

to the following formula: $I_{DEM} \approx \frac{V_{aux}}{R_{DEM}} \approx \frac{N \times V_{mains}}{R_{DEM}}$

where: N = $\frac{N_{aux}}{N_{p}}$

The current information is used to adjust the peak drain current, which is measured via pin I_{sense} . The internal compensation is such that an almost mains independent maximum output power can be realized.

The OPP curve is given in Fig.10.

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT

Short winding protection

After the leading edge blanking time, the short winding protection circuit is activated. If the 'sense' voltage exceeds the short winding protection voltage V_{swp} , the converter will stop switching. Once V_{CC} drops below the UVLO level, capacitor C_{VCC} will be recharged and the supply will restart again. This cycle will be repeated until the short-circuit is removed (safe restart mode).

The short winding protection will also protect in case of a secondary diode short-circuit.

OverTemperature Protection (OTP)

An accurate temperature protection is provided in the circuit. When the junction temperature exceeds the thermal shutdown temperature, the IC will enter the safe restart mode.

When the V_{start} level is reached, switching starts again. This process is repeated as long as the OTP condition exists.

Control pin protection

If pin CTRL is open-circuit or not connected, a fault condition is assumed and the converter will stop switching. Operation will recommence as soon as the fault condition is removed.

Soft start-up

To prevent transformer rattle during hiccup, the transformer peak current is slowly increased by the soft start function. This can be achieved by inserting a resistor and a capacitor between pin I_{sense} and the sense resistor (see Fig.11). An internal current source charges the capacitor to V = I_{SS} × R_{SS}, with a maximum of approximately 0.5 V.

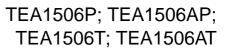
The start level and the time constant of the increasing primary current level can be adjusted externally by changing the values of R_{SS} and C_{SS} .

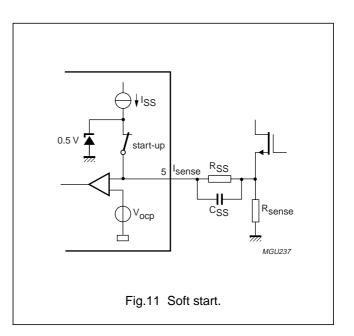
$$I_{primary(max)} = \frac{V_{ocp} - (I_{SS} \times R_{SS})}{R_{sense}}$$

 $\tau ~=~ \textbf{R}_{\text{SS}} \times \textbf{C}_{\text{SS}}$

The charging current I_{SS} will flow as long as the voltage on pin I_{sense} is below approximately 0.5 V. If the voltage on pin I_{sense} exceeds 0.5 V, the soft start current source will start limiting the current I_{SS}. At the V_{CC(start)} level, the I_{SS} current source is completely switched off.

Since the soft start current $I_{\rm SS}$ is supplied from pin DRAIN, the $R_{\rm SS}$ value will not affect the $V_{\rm CC}$ current during start-up.





Driver

The driver circuit to the gate of the power MOSFET has a current sourcing capability of 135 mA typical and a current sink capability of 560 mA typical. This permits fast turn-on and turn-off of the power MOSFET for efficient operation.

A low driver source current has been chosen to limit the $\Delta V/\Delta t$ at switch-on. This reduces Electro Magnetic Interference (EMI) and also limits the current spikes across $R_{sense}.$

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); note 1.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Voltages			I		ł
V _{CC}	supply voltage	continuous	-0.4	+20	V
V _{CTRL}	voltage on pin CTRL		-0.4	+5	V
V _{DEM}	voltage on pin DEM	current limited	-0.4	-	V
V _{sense}	voltage on pin I _{sense}	current limited	-0.4	-	V
V _{DRAIN}	voltage on pin DRAIN		-0.4	+650	V
Currents					
I _{CTRL}	current on pin CTRL		_	5	mA
I _{DEM}	current on pin DEM		-250	+250	μA
I _{sense}	current on pin I _{sense}		-1	+10	mA
I _{DRIVER}	current on pin DRIVER	d < 10 %	-0.8	+2	A
I _{DRAIN}	current on pin DRAIN		-	5	mA
General				•	•
P _{tot}	total power dissipation	T _{amb} < 70 °C	-	0.75	W
T _{stg}	storage temperature		-55	+150	°C
Tj	operating junction temperature		-20	+145	°C
V _{esd}	electrostatic discharge voltage				
	all pins except pins DRAIN and $V_{\mbox{CC}}$	HBM class 1; note 2	-	2000	V
	pins DRAIN and V _{CC}	HBM class 1; note 2	_	1500	V
	any pin	MM; note 3	_	400	V

Notes

 All voltages are measured with respect to ground; positive currents flow into the IC; pin V_{CC} may not be current driven. The voltage ratings are valid provided other ratings are not violated; current ratings are valid provided the maximum power rating is not violated.

- 2. Human Body Model (HBM): equivalent to discharging a 100 pF capacitor through a 1.5 k Ω resistor.
- 3. Machine Model (MM): equivalent to discharging a 200 pF capacitor through a 0.75 μ H coil and a 10 Ω resistor.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	100	K/W

QUALITY SPECIFICATION

In accordance with 'SNW-FQ-611-D'.

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT

CHARACTERISTICS

 T_{amb} = 25 °C; V_{CC} = 15 V; all voltages are measured with respect to ground; currents are positive when flowing into the IC; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Start-up currer	nt source (pin DRAIN)	I	•			1
I _{DRAIN}	supply current drawn from	V _{CC} < V _{start}	_	500	-	μA
	pin DRAIN	V _{CC} > V _{start}	-	50	-	μA
BV _{DSS}	breakdown voltage		650	_	_	V
Supply voltage	management (pin V _{CC})					
V _{CC(start)}	start-up voltage on V _{CC}		10.3	11	11.7	V
V _{CC(UVLO)}	undervoltage lock-out on V _{CC}		8.1	8.7	9.3	V
V _{CC(hys)}	hysteresis voltage on V _{CC}	V _{CC(start)} – V _{CC(UVLO)}	2.0	2.3	2.6	V
I _{CC(oper)}	supply current under normal operation	no load on pin DRIVER	1.1	1.3	1.5	mA
I _{CC(start)}	supply current in start-up and safe restart mode	V _{CC} < V _{start}	0 ⁽¹⁾	-	70	μA
I _{CC(protection)}	supply current while not switching	$V_{CC} > V_{UVLO}$	-	0.85	_	mA
Demagnetizati	on management (pin DEM)					
V _{th(DEM)}	demagnetization comparator threshold voltage on pin DEM		50	100	150	mV
Iprot(DEM)	protection current on pin DEM	V _{DEM} = 50 mV	-50 ⁽²⁾	-	-10	nA
V _{clamp(DEM)(neg)}	negative clamp voltage on pin DEM	I _{DEM} = –150 μA	-0.5	-0.25	-0.05	V
V _{clamp(DEM)(pos)}	positive clamp voltage on pin DEM	I _{DEM} = 250 μA	0.5	0.7	0.9	V
t _{suppr}	suppression of transformer ringing at start of secondary stroke		1.1	1.5	1.9	μs
Pulse width me	odulator					
t _{on(min)}	minimum on-time		_	t _{leb}	_	ns
t _{on(max)}	maximum on-time	latched	40	50	60	μs
Oscillator						!
f _{osc(I)}	oscillator low fixed frequency	V _{CTRL} > 1.5 V	20	25	30	kHz
f _{osc(h)}	oscillator high fixed frequency	V _{CTRL} < 1 V	145	175	205	kHz
V _{vco(start)}	peak voltage on pin I _{sense} ; where frequency reduction starts	see Figs 7 and 8	-	VCO ₁	-	mV
V _{vco(nom)}	peak voltage on pin I _{sense} ; where the frequency is equal to f _{osc(l)}		-	VCO ₁ – 50	-	mV
Duty cycle con	trol (pin CTRL)	1			1	1
V _{CTRL(min)}	minimum voltage on pin CTRL for maximum duty cycle		-	1.0	-	V
V _{CTRL(max)}	maximum voltage on pin CTRL for minimum duty cycle		-	1.5	-	V
Iprot(CTRL)	protection current on pin CTRL	V _{CTRL} = 1.5 V	-1 ⁽²⁾	-0.8	-0.5	μA

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Valley switch	(pin DRAIN)	1		1		
$\Delta V / \Delta t_{valley}$	valley recognition voltage change		-85	-	+85	V/µs
t _{valley} -swon	delay from valley recognition to switch-on		-	150 ⁽²⁾	-	ns
Overcurrent a	nd short winding protection (pin I _{se}	nse)	·			
V _{sense(max)}	maximum source voltage OCP	$\Delta V/\Delta t = 0.1 V/\mu s$	0.48	0.52	0.56	V
t _{PD}	propagating delay from detecting V _{sense(max)} to switch-off	$\Delta V/\Delta t = 0.5 V/\mu s$	-	140	185	ns
V _{swp}	short winding protection voltage		0.83	0.88	0.96	V
t _{leb}	blanking time for current and short winding protection		300	370	440	ns
I _{SS}	soft start current	V _{sense} < 0.5 V	45	60	75	μA
Overvoltage p	protection (pin DEM)	•	•			•
I _{OVP(DEM)}	OVP level on pin DEM	set by resistor R _{DEM} ; see Section "OverVoltage Protection (OVP)"	54	60	66	μA
Overpower pr	otection (pin DEM)					
I _{OPP(DEM)}	OPP current on pin DEM to start OPP correction	set by resistor R _{DEM} ; see Section "OverPower Protection (OPP)"	_	-24	-	μA
I _{OPP50%} (DEM)	OPP current on pin DEM; where maximum source voltage is limited to 0.3 V		-	-100	-	μA
Driver (pin DR	liver)		•			•
I _{source}	source current capability of driver	V _{CC} = 9.5 V; V _{DRIVER} = 2 V	-	-135	-	mA
l _{sink}	sink current capability of driver	V _{CC} = 9.5 V; V _{DRIVER} = 2 V	-	240	-	mA
		V _{CC} = 9.5 V; V _{DRIVER} = 9.5 V	-	560	-	mA
V _{o(max)}	maximum output voltage of the driver	V _{CC} > 12 V	-	11.5	12	V
Overtemperat	ure protection					
T _{prot(max)}	maximum temperature protection level		130	140	150	°C
T _{prot(hys)}	hysteresis for the temperature protection level		-	8(2)	_	°C

Notes

1. For $V_{CC} \ge 2 V$.

2. Guaranteed by design.

TEA1506P; TEA1506AP;

TEA1506T; TEA1506AT

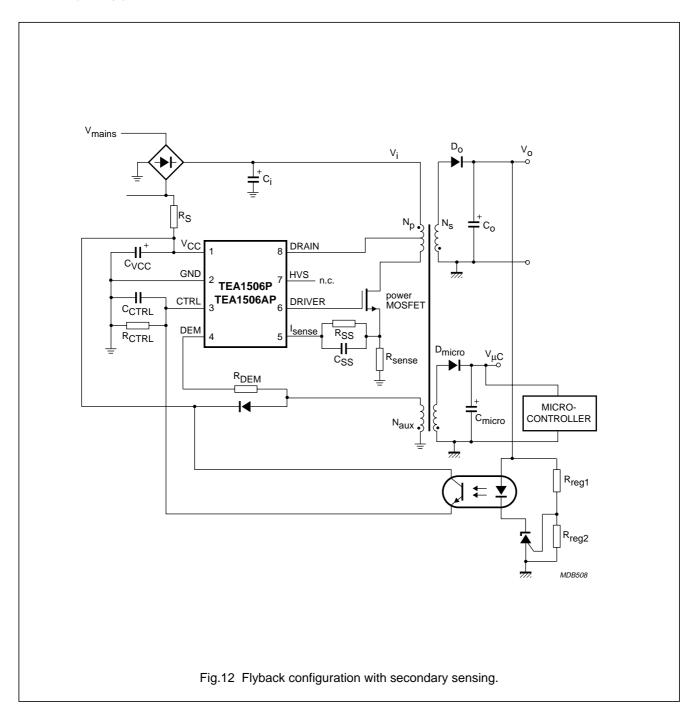
GreenChip™II SMPS control IC

APPLICATION INFORMATION

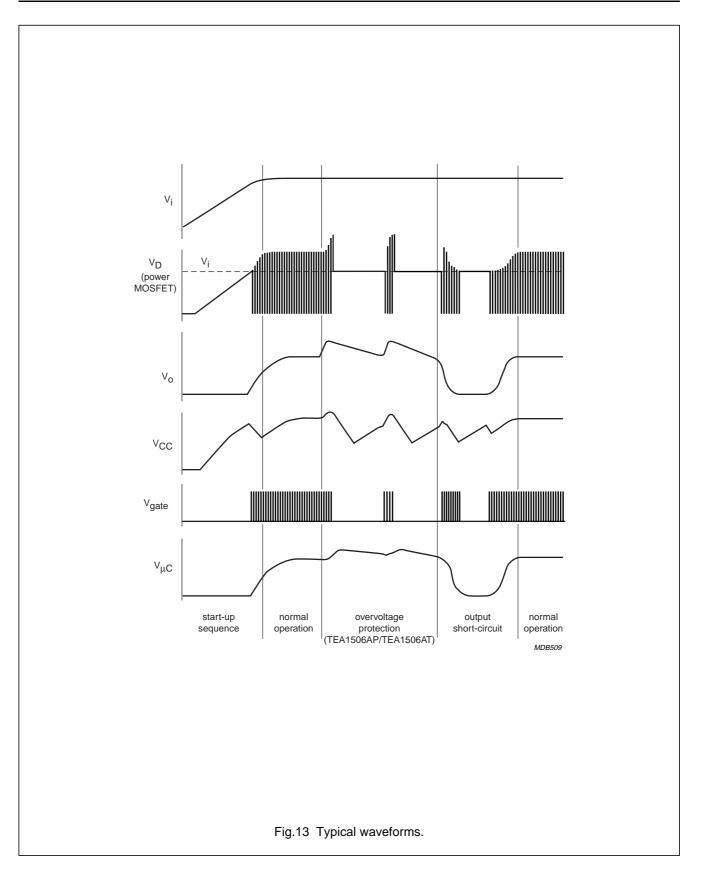
A converter with the TEA1506 consists of an input filter, a transformer with a third winding (auxiliary), and an output stage with a feedback circuit.

Capacitor C_{VCC} (at pin V_{CC}) buffers the supply voltage of the IC, which is powered via the resistor R_S during start-up and via the auxiliary winding during operation.

A sense resistor converts the primary current into a voltage at pin I_{sense}. The value of this sense resistor defines the maximum primary peak current.



TEA1506P; TEA1506AP; TEA1506T; TEA1506AT



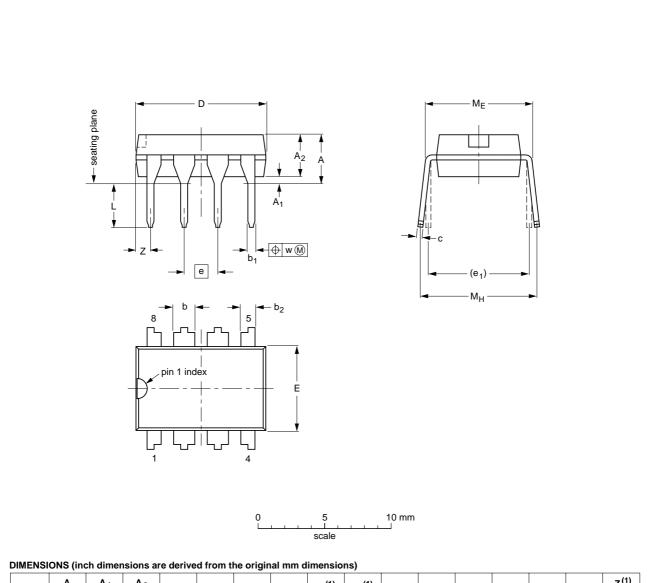
TEA1506P; TEA1506AP;

TEA1506T; TEA1506AT

GreenChip™II SMPS control IC

PACKAGE OUTLINES

DIP8: plastic dual in-line package; 8 leads (300 mil)



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	с	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.14	0.53 0.38	1.07 0.89	0.36 0.23	9.8 9.2	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	1.15
inches	0.17	0.02	0.13	0.068 0.045	0.021 0.015	0.042 0.035	0.014 0.009	0.39 0.36	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.045

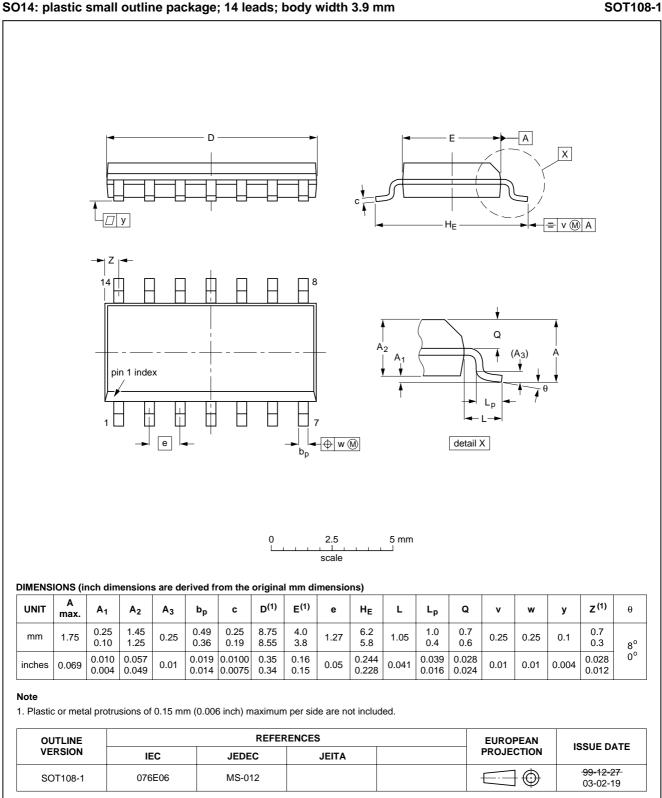
Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC JEITA			PROJECTION	ISSUE DATE	
SOT97-1	050G01	MO-001	SC-504-8			99-12-27 03-02-13	

SOT97-1

TEA1506P; TEA1506AP; TEA1506T; TEA1506AT



SOLDERING

Introduction

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "*Data Handbook IC26; Integrated Circuit Packages*" (document order number 9398 652 90011).

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mount components are mixed on one printed-circuit board. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended. Driven by legislation and environmental forces the worldwide use of lead-free solder pastes is increasing.

Through-hole mount packages

SOLDERING BY DIPPING OR BY SOLDER WAVE

Typical dwell time of the leads in the wave ranges from 3 to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ($T_{stg(max)}$). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

MANUAL SOLDERING

Apply the soldering iron (24 V or less) to the lead(s) of the package, either below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 $^{\circ}$ C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 $^{\circ}$ C, contact may be up to 5 seconds.

Surface mount packages

REFLOW SOLDERING

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and

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cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferably be kept:

- below 220 °C (SnPb process) or below 245 °C (Pb-free process)
 - for all the BGA and SSOP-T packages
 - for packages with a thickness \geq 2.5 mm
 - for packages with a thickness < 2.5 mm and a volume ≥ 350 mm³ so called thick/large packages.
- below 235 °C (SnPb process) or below 260 °C (Pb-free process) for packages with a thickness < 2.5 mm and a volume < 350 mm³ so called small/thin packages.

Moisture sensitivity precautions, as indicated on packing, must be respected at all times.

WAVE SOLDERING

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe

dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time of the leads in the wave ranges from 3 to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

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MANUAL SOLDERING

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

MOUNTING		SOLDERING METHOD					
MOONTING	PACKAGE	WAVE	REFLOW ⁽²⁾	DIPPING			
Through-hole mount	DBS, DIP, HDIP, SDIP, SIL	suitable ⁽³⁾	-	suitable			
Through-hole- surface mount	PMFP ⁽⁹⁾	not suitable	not suitable	_			
Surface mount	BGA, LBGA, LFBGA, SQFP, SSOP-T ⁽⁴⁾ , TFBGA, VFBGA	not suitable	suitable	_			
	DHVQFN, HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽⁵⁾	suitable	-			
	PLCC ⁽⁶⁾ , SO, SOJ	suitable	suitable	_			
	LQFP, QFP, TQFP	not recommended ⁽⁶⁾⁽⁷⁾	suitable	_			
	SSOP, TSSOP, VSO, VSSOP	not recommended ⁽⁸⁾	suitable	_			

Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. For SDIP packages, the longitudinal axis must be parallel to the transport direction of the printed-circuit board.
- 4. These transparent plastic packages are extremely sensitive to reflow soldering conditions and must on no account be processed through more than one soldering cycle or subjected to infrared reflow soldering with peak temperature exceeding 217 °C ± 10 °C measured in the atmosphere of the reflow oven. The package body peak temperature must be kept as low as possible.
- 5. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 7. Wave soldering is suitable for LQFP, QFP and TQFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 8. Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.
- 9. Hot bar soldering or manual soldering is suitable for PMFP packages.

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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